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# Thyristor High Voltage Surface Mount Phase Control SCR, 10 A



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 6.5 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V						
$V_{TM}$	< 1.15 V						
I <sub>GT</sub>	15 mA						
T <sub>J</sub>	-40 to +125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

#### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-10TTS08S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5							

#### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	6.5	^					
I <sub>RMS</sub>		10	A					
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V					
I <sub>TSM</sub>		110	A					
V <sub>T</sub>	6.5 A, T <sub>J</sub> = 25 °C	1.15	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
T <sub>J</sub>	Range	-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-10TTS08S-M3	800	800	1.0						



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PARAMETER	SYMBOL	TEST CONI	VALUES	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T 440 % 400% and water	6.5		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	$T_C = 112  ^{\circ}\text{C},  180^{\circ}  \text{conduction}$	on hall sine wave	10	Α
Maximum peak, one-cycle,	_	10 ms sine pulse, rated V <sub>RR</sub>	<sub>IM</sub> applied, T <sub>J</sub> = 125 °C	95	l A
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage	e reapplied, T <sub>J</sub> = 125 °C	110	
Maximum 12t fau fuaina	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RR</sub>	<sub>IM</sub> applied, T <sub>J</sub> = 125 °C	45	A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no voltage	e reapplied, T <sub>J</sub> = 125 °C	64	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no volta	640	A²√s	
Maximum on-state voltage drop	$V_{TM}$	6.5 A, T <sub>J</sub> = 25 °C	1.15	V	
On-state slope resistance	r <sub>t</sub>	T 105 00		17.3	mΩ
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		0.85	V
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	\/ - ratad \/ \	0.05	
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	1.0	
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, resistiv $T_J = 25 ^{\circ}\text{C}$	30	mA	
Maximum latching current	ΙL	Anode supply = 6 V, resistiv	50		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \%$		V/µs	
Maximum rate of rise of turned-on current	dl/dt		-	100	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	l vv	
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1		
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V	0.2	1	
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	0.1	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	3	μs
Typical turn-off time	tq	1 1 = 125 0	100	



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THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/VV				
Approximate weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	10TTS	08S				

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

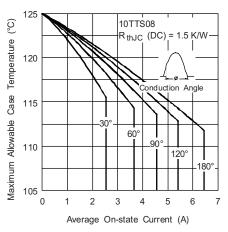


Fig. 1 - Current Rating Characteristics

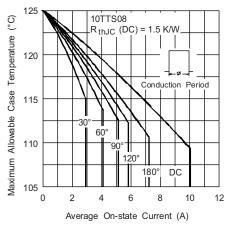


Fig. 2 - Current Rating Characteristics

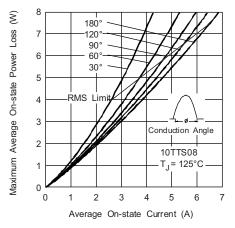


Fig. 3 - On-State Power Loss Characteristics

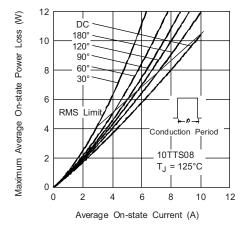


Fig. 4 - On-State Power Loss Characteristics

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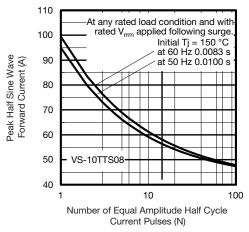


Fig. 5 - Maximum Non-Repetitive Surge Current

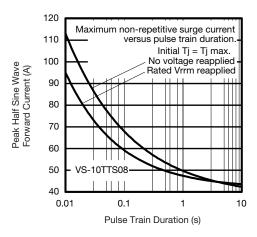


Fig. 6 - Maximum Non-Repetitive Surge Current

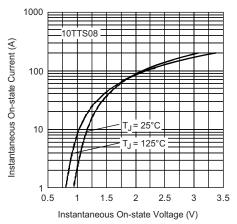


Fig. 7 - On-State Voltage Drop Characteristics

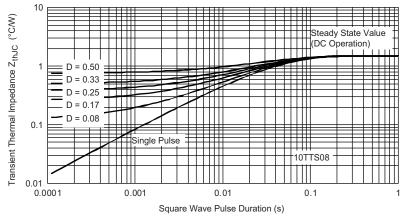


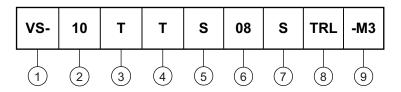
Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics



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### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = single thyristor

4 - Package:

 $T = D^2PAK (TO-263AB)$ 

5 - Type of silicon:

S = converter grade

6 - Voltage code x 100 = V<sub>RRM</sub>

7 - S = surface mountable

8 - Tape and reel option:

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-10TTS08S-M3	50	1000	Antistatic plastic tubes					
VS-10TTS08STRR-M3	800	800	13" diameter reel					
VS-10TTS08STRL-M3	800	800	13" diameter reel					

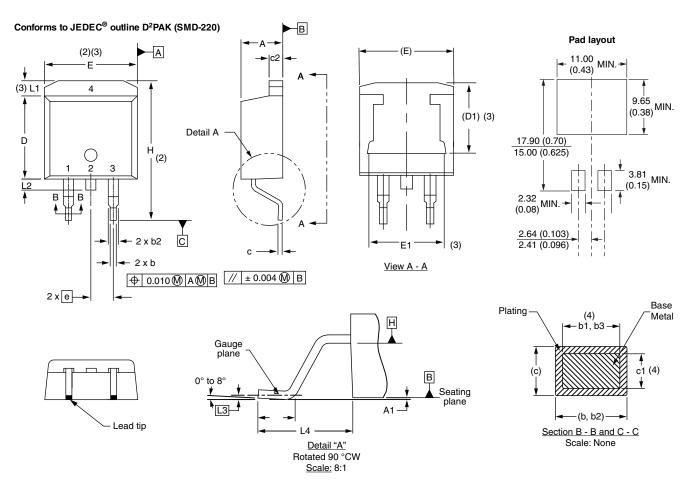
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96164</u>						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



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# D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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